Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

Complementary 30 V (G-S) MOSFET

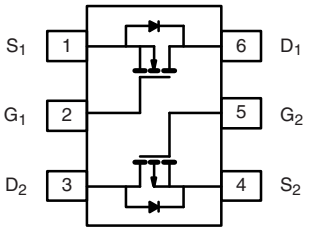
PRODUCT SUMMARY			
	V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
N-Channel	30	0.480 at V_{GS} = 10 V	0.63
		0.700 at V_{GS} = 4.5 V	0.52
P-Channel	- 30	0.940 at V_{GS} = - 10 V	- 0.45
		1.700 at V_{GS} = - 4.5 V	- 0.33

FEATURES

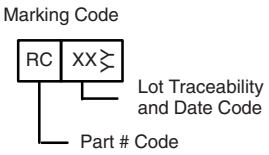
- TrenchFET® Power MOSFET
- Material categorization:
  For definitions of compliance please see www.vishay.com/doc?99912

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

SOT-363
SC-70 (6-LEADS)



Top View



Ordering Information: Si1539DL-T1-E3 (Lead (Pb)-free)
Si1539DL-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)							
Parameter		Symbol	N-Channel		P-Channel		Unit
			5 s	Steady State	5 s	Steady State	
Drain-Source Voltage		V_{DS}	30		- 30		V
Gate-Source Voltage		V_{GS}	± 20				
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	0.63	0.54	- 0.45	- 0.42	A
	T_A = 85 °C		0.45	0.43	- 0.32	- 0.31	
Pulsed Drain Current		I_{DM}	1				
Continuous Source Current (Diode Conduction)[a]		I_S	0.25	0.23	- 0.25	- 0.23	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	0.30	0.27	0.30	0.27	W
	T_A = 85 °C		0.16	0.14	0.16	0.14	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150				°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a]	t ≤ 5 s	R_{thJA}	360	415	°C/W
	Steady State		400	460	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	300	350	

Notes:
a. Surface mounted on 1" x 1" FR4 board.

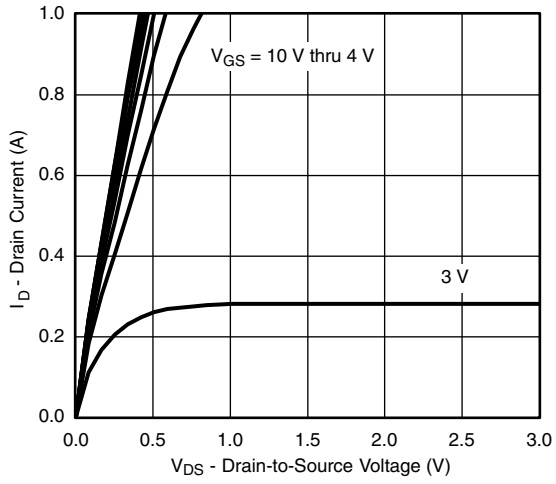
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

Parameter	Symbol	Test Conditions		Min.	Typ.	Max.	Unit
Static							
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	N-Ch	1		2.6	V
		V_{DS} = V_{GS}, I_D = - 250 µA	P-Ch	- 1		- 2.6	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	N-Ch			± 100	nA
			P-Ch			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24 V, V_{GS} = 0 V	N-Ch			1	µA
		V_{DS} = - 24 V, V_{GS} = 0 V	P-Ch			- 1	
		V_{DS} = 24 V, V_{GS} = 0 V, T_J = 85 °C	N-Ch			5	
		V_{DS} = - 24 V, V_{GS} = 0 V, T_J = 85 °C	P-Ch			- 5	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	N-Ch	1			A
		$V_{DS} \leq$ - 5 V, V_{GS} = - 10 V	P-Ch	- 1			
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 0.59 A	N-Ch		0.410	0.480	Ω
		V_{GS} = - 10 V, I_D = - 0.42 A	P-Ch		0.800	0.940	
		V_{GS} = 4.5 V, I_D = 0.2 A	N-Ch		0.600	0.700	
		V_{GS} = - 4.5 V, I_D = - 0.2 A	P-Ch		1.500	1.700	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 0.59 A	N-Ch		0.75		S
		V_{DS} = - 15 V, I_D = - 0.42 A	P-Ch		0.5		
Diode Forward Voltage[a]	V_{SD}	I_S = 0.23 A, V_{GS} = 0 V	N-Ch		0.80	1.2	V
		I_S = - 0.23 A, V_{GS} = 0 V	P-Ch		- 0.86	- 1.2	
Dynamic[b]							
Total Gate Charge	Q_g	N-Channel V_{DS} = 15 V, V_{GS} = 10 V, I_D = 0.59 A P-Channel V_{DS} = - 15 V, V_{GS} = - 10 V, I_D = - 0.42 A	N-Ch		0.86	1.4	nC
			P-Ch		0.90	1.4	
Gate-Source Charge	Q_{gs}		N-Ch		0.24		
			P-Ch		0.21		
Gate-Drain Charge	Q_{gd}		N-Ch		0.08		
			P-Ch		0.17		
Turn-On Delay Time	$t_{d(on)}$	N-Channel V_{DD} = 15 V, R_L = 30 Ω $I_D \cong$ 0.5 A, V_{GEN} = 10 V, R_g = 6 Ω P-Channel V_{DD} = - 15 V, R_L = 30 Ω $I_D \cong$ - 0.5 A, V_{GEN} = - 10 V, R_g = 6 Ω	N-Ch		5	10	ns
			P-Ch		4	10	
Rise Time	t_r		N-Ch		8	15	
			P-Ch		8	15	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch		8	15	
			P-Ch		5	10	
Fall Time	t_f		N-Ch		7	15	
			P-Ch		7	15	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 0.23 A, dI/dt = 100 A/µs	N-Ch		15	30	
		I_F = - 0.23 A, dI/dt = 100 A/µs	P-Ch		20	40	

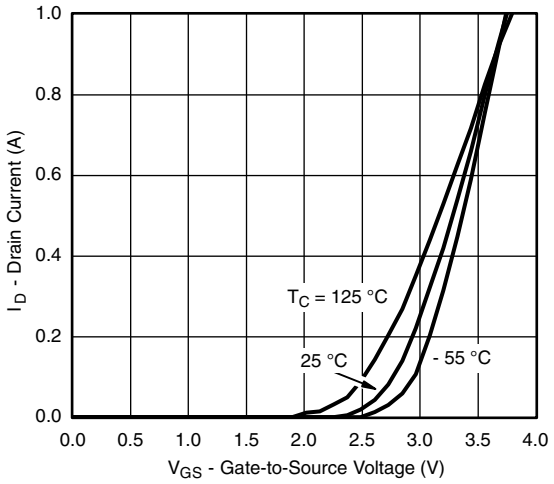
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

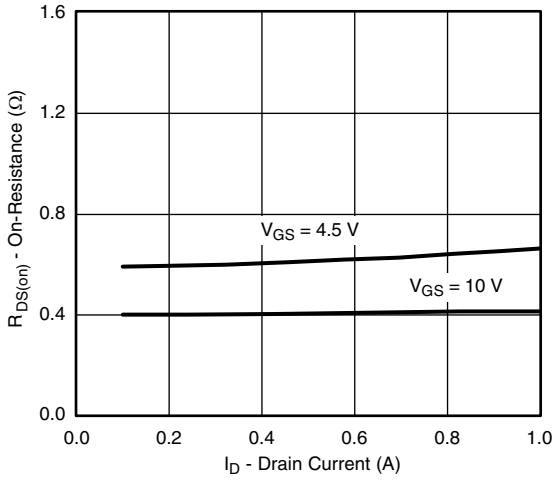
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



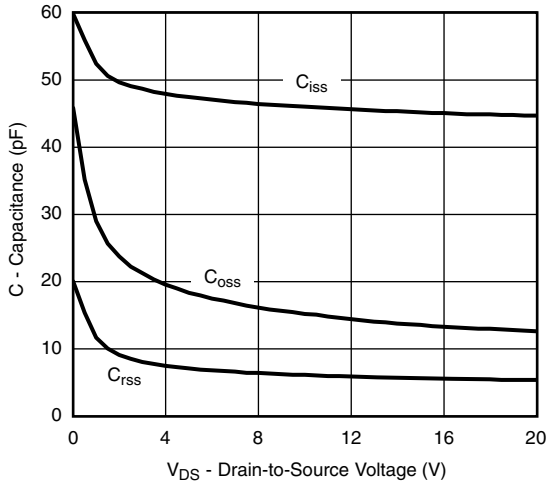
Output Characteristics



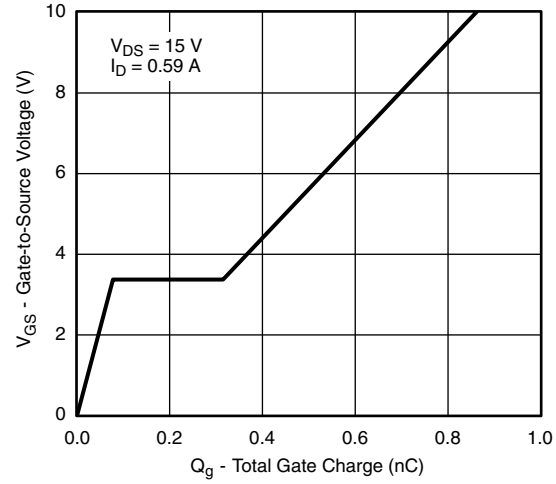
Transfer Characteristics



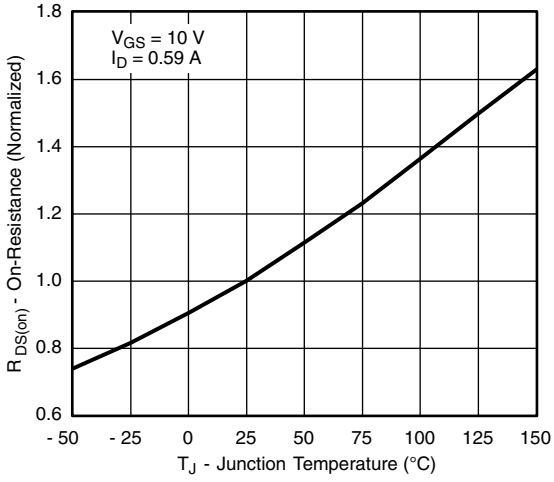
On-Resistance vs. Drain Current



Capacitance

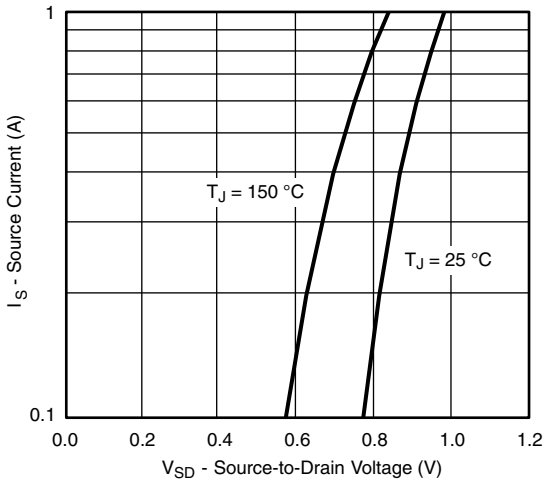


Gate Charge

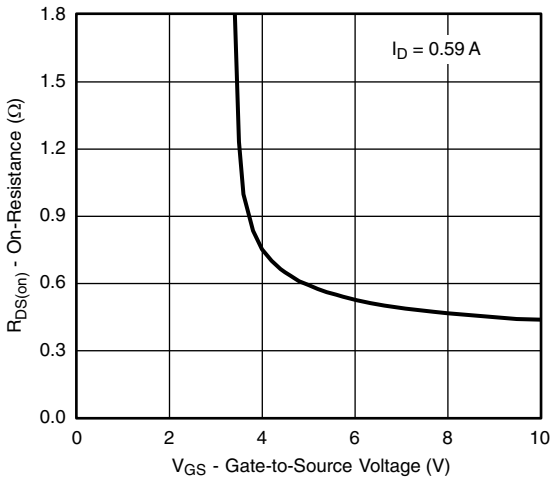


On-Resistance vs. Junction Temperature

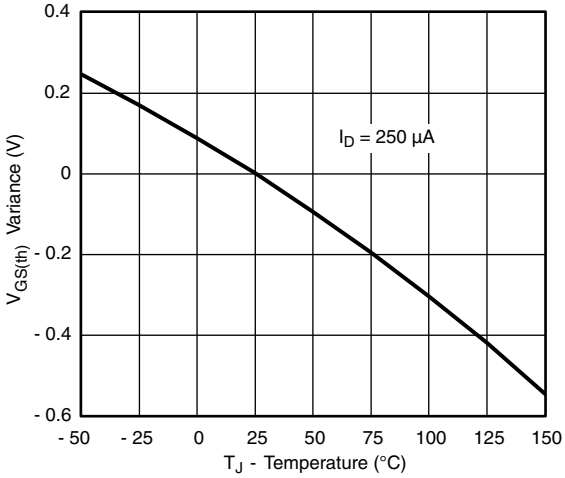
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



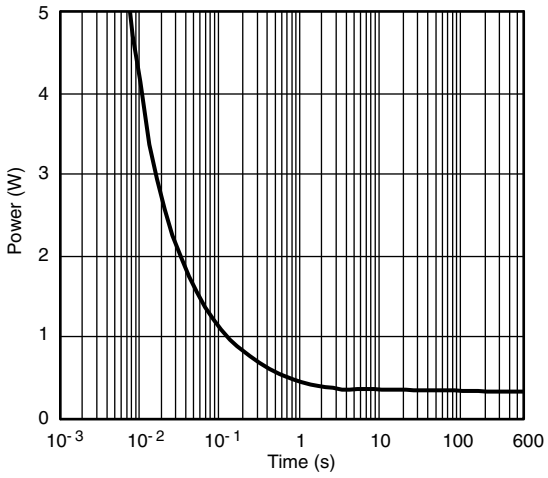
Source-Drain Diode Forward Voltage



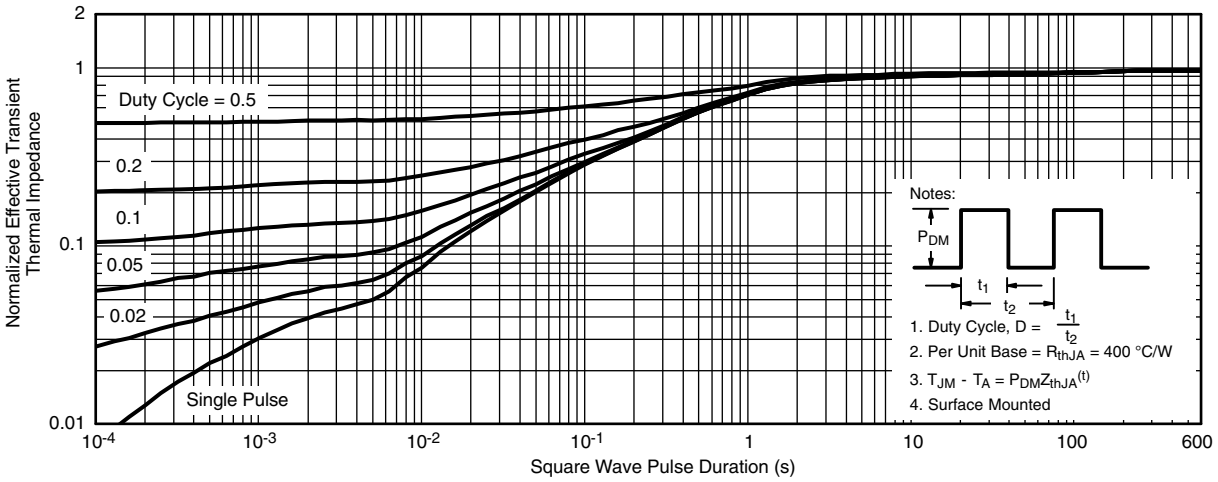
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



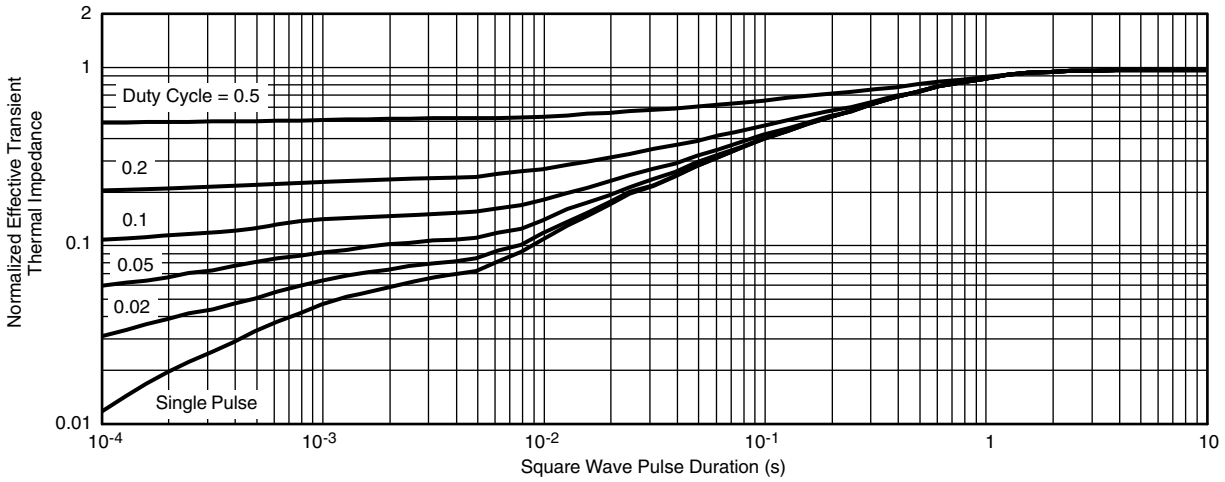
Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

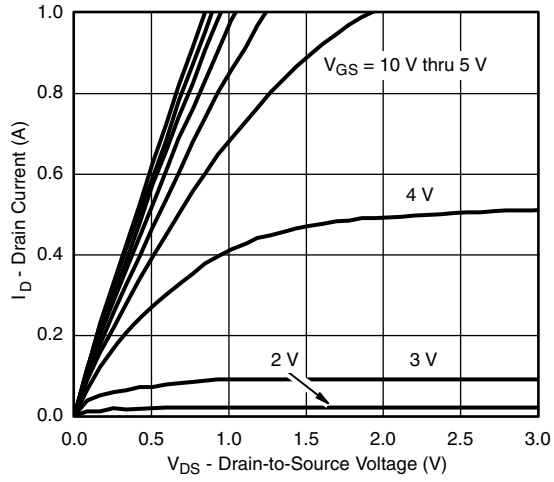
For more information please contact: pmostechsupport@vishay.com
Document Number: 71250
S12-0800-Rev. E, 16-Apr-12

N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

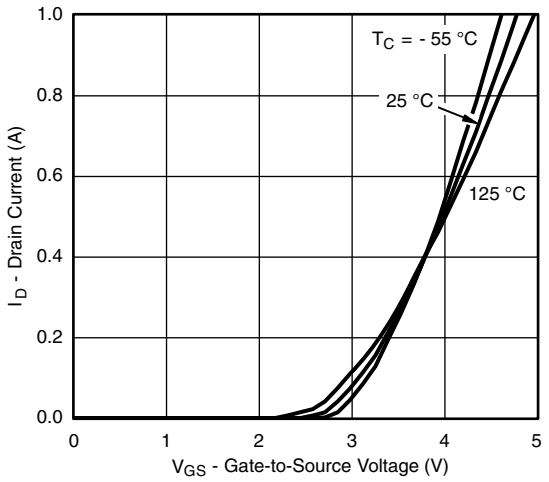


Normalized Thermal Transient Impedance, Junction-to-Foot

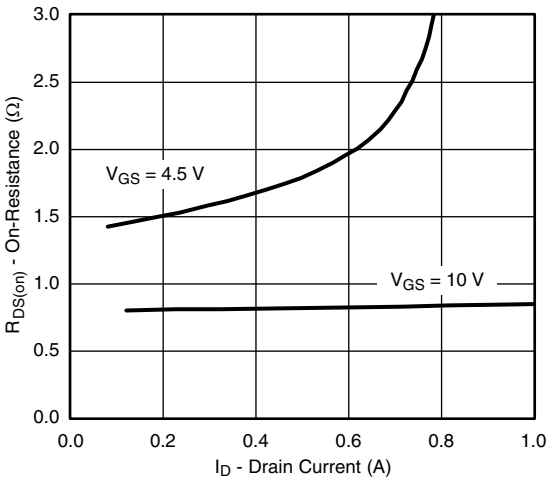
P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



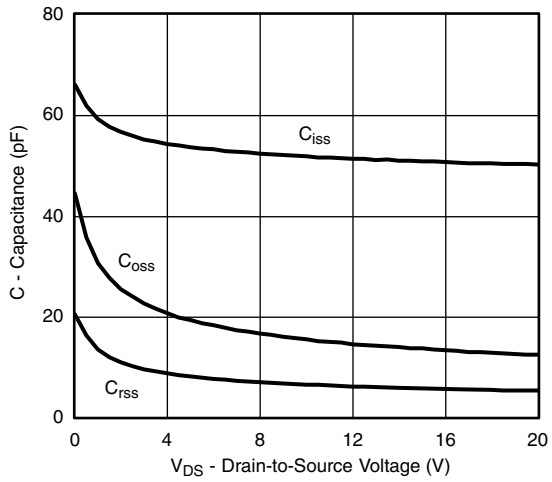
Output Characteristics



Transfer Characteristics

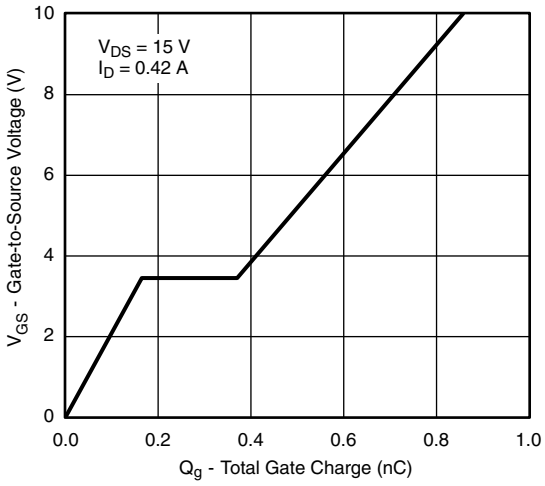


On-Resistance vs. Drain Current

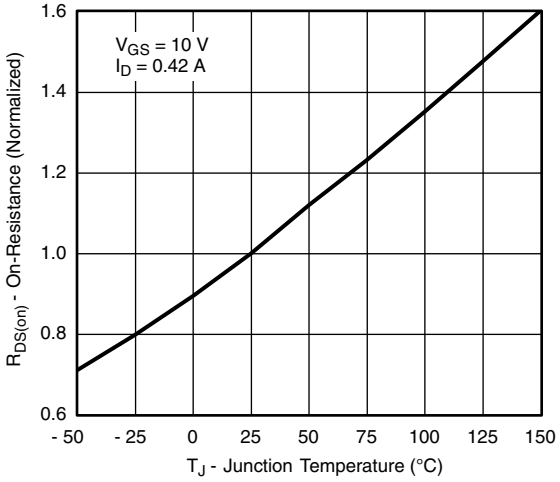


Capacitance

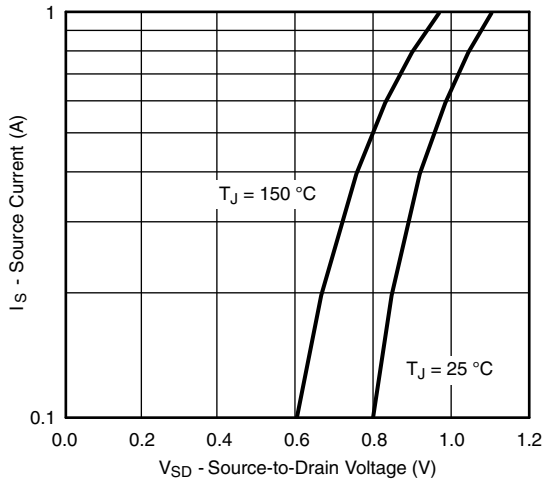
P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



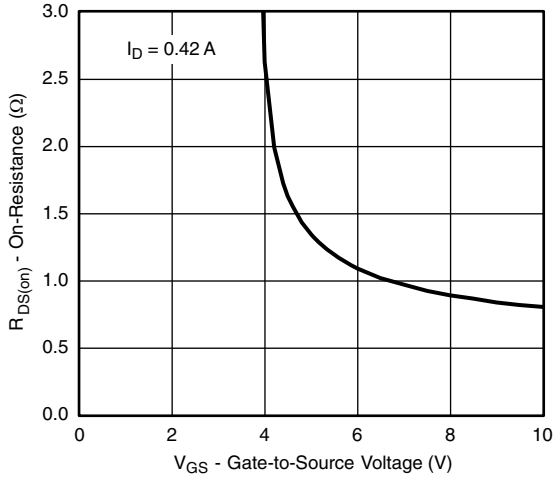
Gate Charge



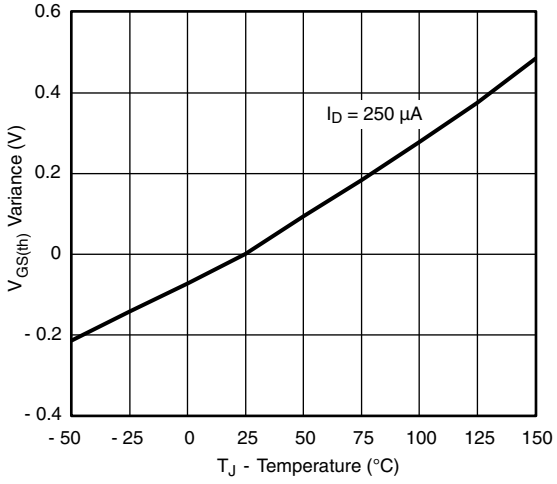
On-Resistance vs. Junction Temperature



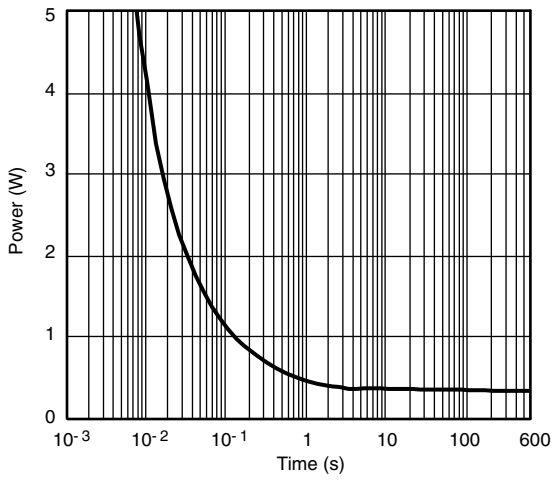
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power

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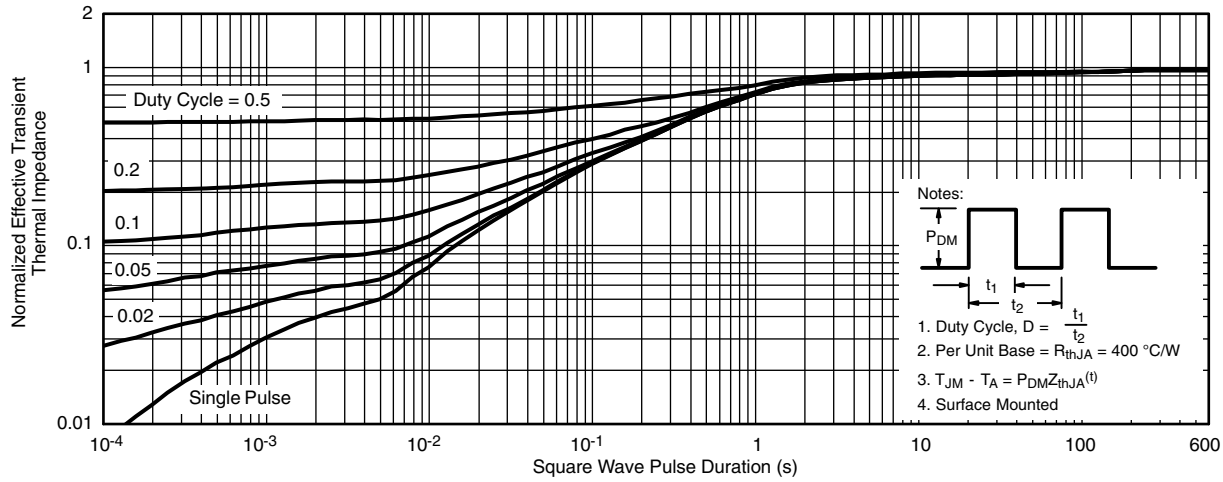
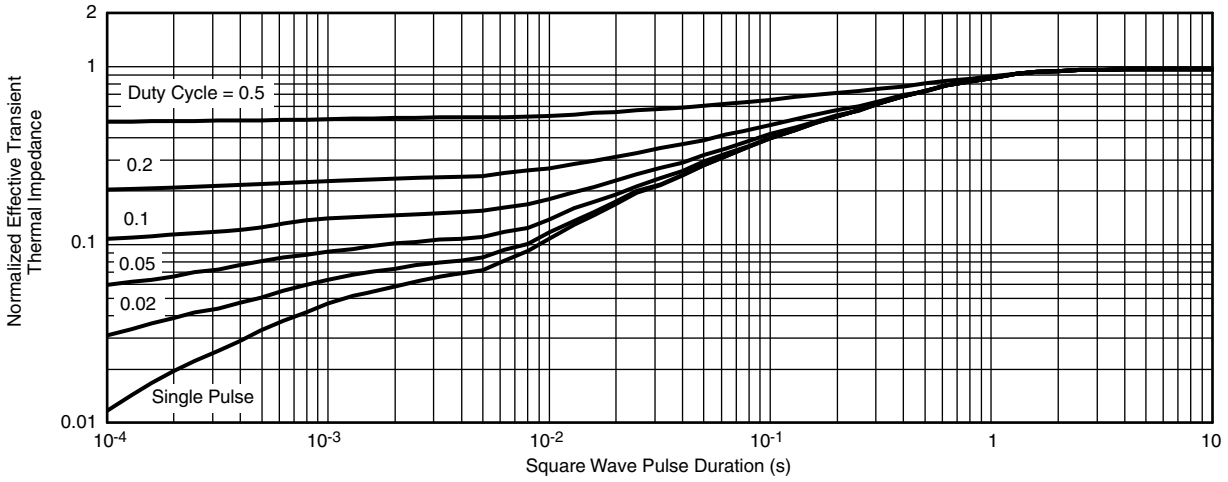
P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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